

WHAT IS CLAIMED IS:

1. A method for making a piezoelectric element comprising a piezoelectric film formed on a substrate by a gas deposition technique, the method comprising the steps of:

ejecting ultra-fine particles of a piezoelectric material having a perovskite structure from an ejecting device toward the substrate; and

applying an electric field to the ultra-fine particles traveling to the substrate.

2. A method for making a piezoelectric element according to Claim 1, wherein the electric field applied has an intensity in the range of 0.5 to 3 kV/mm.

3. A method for making a piezoelectric element according to Claim 2, wherein the electric field applied has an intensity in the range of 1 to 2 kV/mm.

4. A method for making a piezoelectric element according to Claim 1, wherein the substrate comprises a metal.

5. A method for making a piezoelectric element

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according to Claim 1, wherein the substrate comprises a resin.